

NTE621
Silicon Rectifier, General Purpose, High Voltage,
Standard Recovery
(Surface Mount)

Features:

- High Temperature Metallurgically Bonded
- Glass Passivated Junction
- High Temperature Soldering Guaranteed:
 +450°C/5 Seconds at Terminals. Complete Device Submersible Temperature of
 +260°C/10 Seconds in Solder Bath.

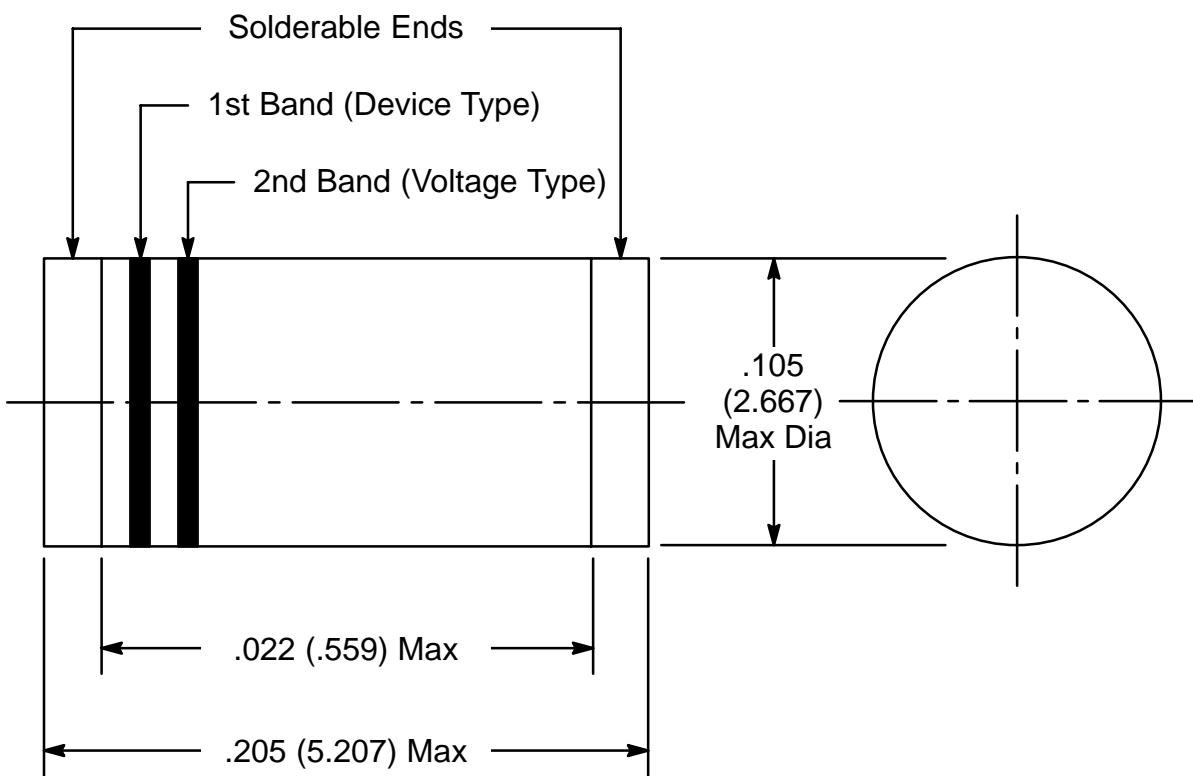
Maximum Ratings and Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified.
 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

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|---|------------------|
| Maximum Recurrent Peak Reverse Voltage, V_{RRM} | 400V |
| Maximum RMS Voltage, V_{RMS} | 280V |
| Maximum DC Blocking Voltage, V_{DC} | 400V |
| Maximum Average Forward Rectified Current, $I_{T(AV)}$ | 1A |
| Peak Forward Surge Current, I_{FSM} (8.3ms Single Half Sine-Wave Superimposed on Rated Load) | 30A |
| Maximum Instantaneous Forward Voltage ($I_T = 1A$), V_F | 1.1V |
| Maximum DC Reverse Current ($V_{DC} = 400V$), I_R | |
| $T_A = +25^\circ\text{C}$ | 10 μA |
| $T_A = +125^\circ\text{C}$ | 50 μA |
| Maximum Full Load Reverse Current (Full Cycle Average at $T_A = +75^\circ\text{C}$), $I_{R(AV)}$ | 30 μA |
| Typical Junction Capacitance (Note 1), C_J | 15pF |
| Operating Junction Temperature Range, T_J | -65° to +175°C |
| Storage Temperature Range, T_{stg} | -65° to +175°C |
| Maximum Thermal Resistance, Junction-to-Terminal (Note 2), R_{thJL} | 30°C/W |
| Maximum Thermal Resistance, Junction-to-Ambient (Note 3), R_{thJA} | 75°C/W |

Note 1. Measured at 1MHz and applied reverse voltage of $4V_{DC}$.

Note 2. Thermal resistance, junction-to-terminal, 6.0mm² copper pads to each terminal.

Note 3. Thermal resistance, junction-to-ambient, 6.0mm² copper pads to each terminal.



Two Bands Indicates Cathode